2. (Currently amended) The method for driving a solid-state image pickup device according to Claim 1, wherein the electric potential of said electric potential barrier during the read-out step is raised up by a voltage greater than 0.4.V.

0.4 ont

- 3. (Currently Amended) The method for driving a solid-state image pickup device according to Claim 1, wherein said signal charges are read out from said photo-electric conversion units through signal read-out portions and the electric potential of said electric potential barrier during the read-out step is deeper than an adjacent electric potential which is applied, applied in signal read-out portion during the times except said read-out step, to said photo electric conversion units which are adjacent to those which are being read out. step.
- 4. (Currently amended) The method for driving a solid-state image pickup device according to Claim 3, wherein the potential difference between said electric potential of said electric potential barrier during the read-out step and said adjacent electric potential which is applied in said signal read-out portion is greater than 0.4 V.
- 5. (Original) The method for driving a solid-state image pickup device according to Claim 1, wherein each of said photoelectric conversion units is provided with a vertical overflow drain (OFD) structure which excludes the surplus charges by said electric potential barrier by a voltage applied to a substrate of said vertical OFD structure, which comprises the steps of:

cutting off said incident light;
raising up said electric potential barrier;
starting reading out said signal charges.

**6.(Currently amended)** The method for driving a solid-state image pickup device according to Claim 5, wherein the electric potential of said electric potential barrier during the read-out step is raised up by a voltage greater than 0.4V.

O.4

- 7. (Currently amended) The method for driving a solid-state image pickup device according to Claim 5, wherein said signal charges are read out from said photo-electric conversion units through signal read-out portions and the electric potential of said electric potential barrier during the read-out step is deeper than an adjacent-electric potential which is applied, applied in signal read-out portion during the times except said read-out step, to said photo-electric conversion units which are adjacent to those which are being read-out. step.
- 8. (Currently amended) The method for driving a solid-state image pickup device according to Claim 7, wherein the potential difference between said electric potential of said electric potential barrier during the read-out step and said-adjacent electric potential which is applied in said signal read-out portion is greater than 0.4V.
- 9. (Original) The method for driving a solid-state image pickup device according to Claim 1, wherein each of said photo-electric conversion units is provided with a horizontal overflow drain (OFD) structure which excludes the surplus charges by said electric potential barrier by a voltage applied to a gate of said horizontal OFD structure, which comprises the steps of:

cutting off said incident light;
raising up said electric potential barrier;
starting reading out said signal charges.

10. (Currently amended) The method for driving a solid-state image pickup device according to Claim 9, wherein the electric potential of said electric potential barrier during the read-out step is raised up by a voltage greater than 0.4V.

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11. (Currently amended) The method for driving a solid-state image pickup device according to Claim 9, wherein said signal charges are read out from said photo-electric conversion units through signal read-out portions and the electric potential of said electric potential barrier during the read-out step is deeper than an adjacent-electric potential which is applied, applied in signal read-out portion during the times except said read-out step, to said photo-electric conversion units which are adjacent to those which are being read-out, step.

12. (Currently amended) The method for driving a solid-state image pickup device according to Claim 11, wherein the potential difference between said electric potential of said electric potential barrier during the read-out step and said adjacent electric potential which is applied in said signal read-out portion is greater than 0.4V.

## IN THE DRAWINGS

Please replace Figs. 7 to 11 originally filed with Figs. 7 to 11 enclosed with this amendment, subject to the approval of the Examiner. Please add new Fig. 12 enclosed with this amendment, subject to the approval of the Examiner.